

TOSHIBA FAST RECOVERY DIODE SILICON DIFFUSED TYPE

# TFR1N, TFR1T

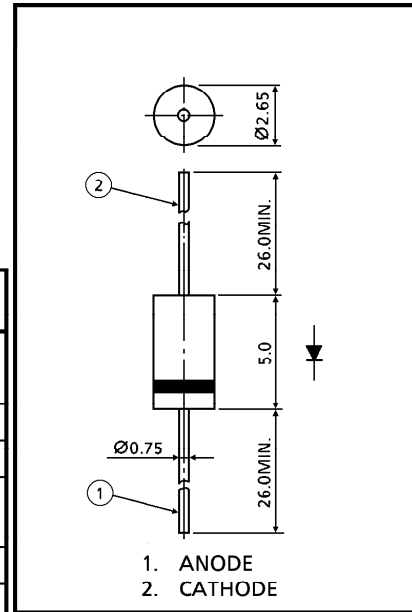
STROBO FLASHER APPLICATIONS. (FAST RECOVERY)

Unit in mm

- Average Forward Current :  $I_F(AV) = 0.5A$
- Repetitive Peak Reverse Voltage :  $V_{RRM} = 1000, 1500V$
- Reverse Recovery Time :  $t_{rr} = 10\mu s$

**MAXIMUM RATINGS**

| CHARACTERISTIC  | SYMBOL    | RATING  | UNIT             |
|---|-----------|---------|------------------|
| Repetitive Peak Reverse Voltage                       | TFR1N     | 1000    | V                |
|   | TFR1T     | 1500    |                  |
| Average Forward Current                               | $I_F(AV)$ | 0.5     | A                |
| $I^2t$ Limit Value (t=1~10ms)                         | $I^2t$    | 2       | A <sup>2</sup> s |
| Peak One Cycle Surge Forward Current (Non Repetitive) | $I_{FSM}$ | 20      | A                |
| Junction Temperature                                  | $T_j$     | -40~125 | °C               |
| Storage Temperature Range                             | $T_{stg}$ | -40~125 | °C               |



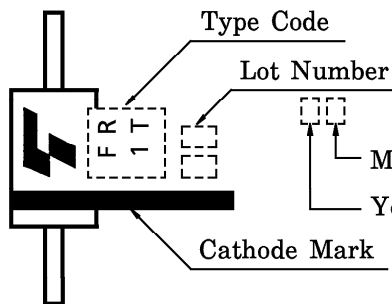
|         |        |
|---------|--------|
| JEDEC   | DO-41  |
| EIAJ    | —      |
| TOSHIBA | 3-3C1A |

**ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

Weight : 0.3g

| CHARACTERISTIC                  | SYMBOL    | TEST CONDITION           | MIN. | TYP. | MAX. | UNIT    |
|---------------------------------|-----------|--------------------------|------|------|------|---------|
| Peak Forward Voltage            | $V_{FM}$  | $I_{FM} = 0.5A$          | —    | —    | 1.3  | V       |
| Repetitive Peak Reverse Current | $I_{RRM}$ | $V_{RRM} = \text{Rated}$ | —    | —    | 10   | $\mu A$ |
| Reverse Recovery Time           | $t_{rr}$  | $I_F = 20mA, I_R = 1mA$  | —    | —    | 10   | $\mu s$ |

**MARKING**

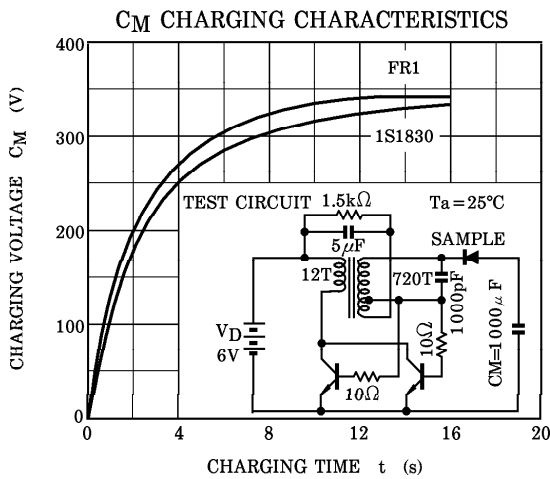
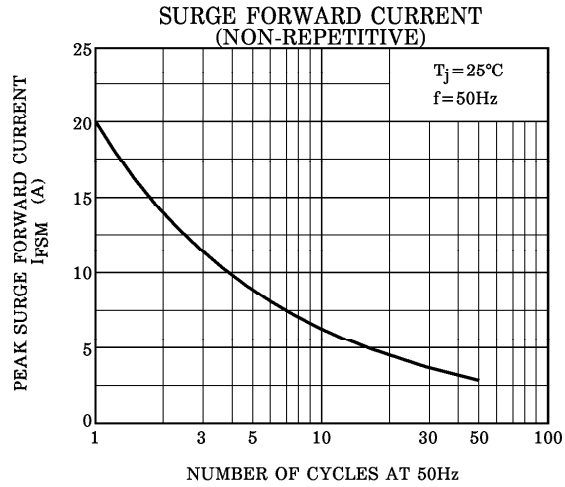
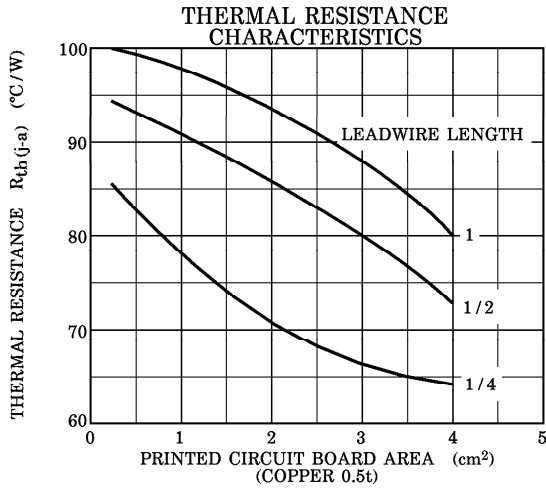
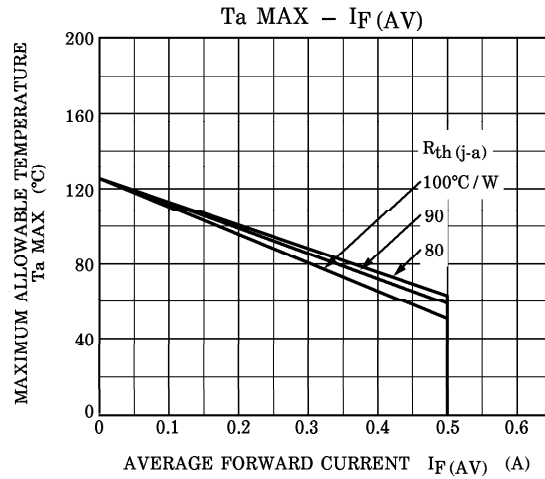
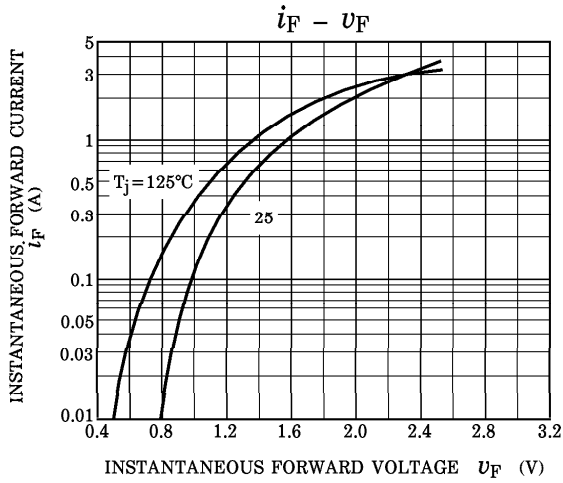


Color : Yellow

| CODE | TYPE  |
|------|-------|
| FR1N | TFR1N |
| FR1T | TFR1T |

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